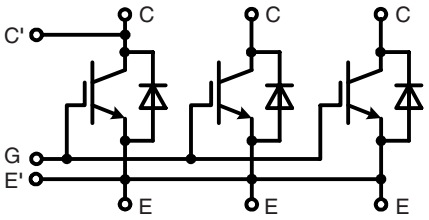
IGBT Module
Single switch

I_{C80} = 1500 A
V_{CES} = 2500 V
$V_{CE(sat)\ typ.}$ = 2.7 V

Short Circuit SOA Capability
Square RBSOA





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IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	V_{GE} = 0 V	2500	V
V_{GES}		± 20	V
I_{C80}	T_C = 80°C	1500	A
I_{CM}	t_p = 1 ms; T_C = 80°C	3000	A
t_{SC}	V_{CC} = 1700 V; $V_{CEM\ CHIP}$ = ≤ 2500 V; V_{GE} ≤ 15 V; T_{VJ} ≤ 125°C	10	µs

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{CE(sat)}$ ①	I_C = 1500 A; V_{GE} = 15 V; T_{VJ} = 25°C		2.7		V
	T_{VJ} = 125°C		3.3		V
$V_{GE(th)}$	I_C = 240 mA; V_{CE} = V_{GE}	6		7.5	V
I_{CES}	V_{CE} = 2500 V; V_{GE} = 0 V; T_{VJ} = 125°C			100	mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V; T_{VJ} = 125°C			500	nA
E_{on}	Inductive load; T_{VJ} = 125°C; V_{GE} = ±15 V;		1400		mJ
E_{off}	V_{CC} = 1200V; I_C = 1500A; R_G = 1.5Ω; L_σ = 100nH		1450		mJ
R_{thJC}				0.008	K/W

① Collector emitter saturation voltage is given at chip level

Features

- NPT³ IGBT
  - Low-loss
  - Smooth switching waveforms for good EMC
- Industry standard package
  - High power density
  - AlSiC base-plate for high power cycling capacity
  - AlN substrate for low thermal resistance

Typical Applications

- AC power converters for
  - industrial drives
  - windmills
  - traction
- LASER pulse generator

IXYS reserves the right to change limits, test conditions and dimensions.

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Diode

Symbol	Conditions	Maximum Ratings	
I_{F80}	T_C = 80°C	1500	A
I_{FSM}	V_R = 0 V; T_{VJ} = 125°C; t_p = 10 ms; half-sinewave	13000	A

Symbol	Conditions	Characteristic Values min.	typ.	max.	
V_F ②	I_F = 1500 A; T_{VJ} = 25°C		2.30		V
	T_{VJ} = 125°C		2.35		V
I_{RM}	V_{CC} = 1200 V; I_C = 1500 A;		1100		A
t_{rr}	V_{GE} = ±15 V; R_G = 1.5 Ω; T_{VJ} = 125°C		1500		ns
Q_{RR}	Inductive load; L_σ = 100nH		925		µC
E_{rec}			800		mJ
R_{thJC}				0.016	K/W

② Forward voltage is given at chip level

Module

Symbol	Conditions		Maximum Ratings	
T_{JM}	max junction temperature		+150	°C
T_{VJ}	Operating temperature		-40...+125	°C
T_{stg}	Storage temperature		-40...+125	°C
V_{ISOL}	50 Hz		5000	V~
M_d	Mounting torque	Base-heatsink, M6 screws	4 - 6	Nm
		Main terminals, M8 screws	8 - 10	Nm

Symbol	Conditions		Characteristic Values min.	typ.	max.	
d_A	Clearance distance	terminal to base	23			mm
		terminal to terminal	19			mm
d_S	Surface creepage	terminal to base	33			mm
	distance	terminal to terminal	33			mm
L_σ	Module stray inductance, C to E terminal			10		nH
$R_{term-chip}$ *	Resistance terminal to chip			0.12		mΩ
R_{thCH}	per module; λ grease = 1 W/m•K			0.006		K/W
Weight				1500		g

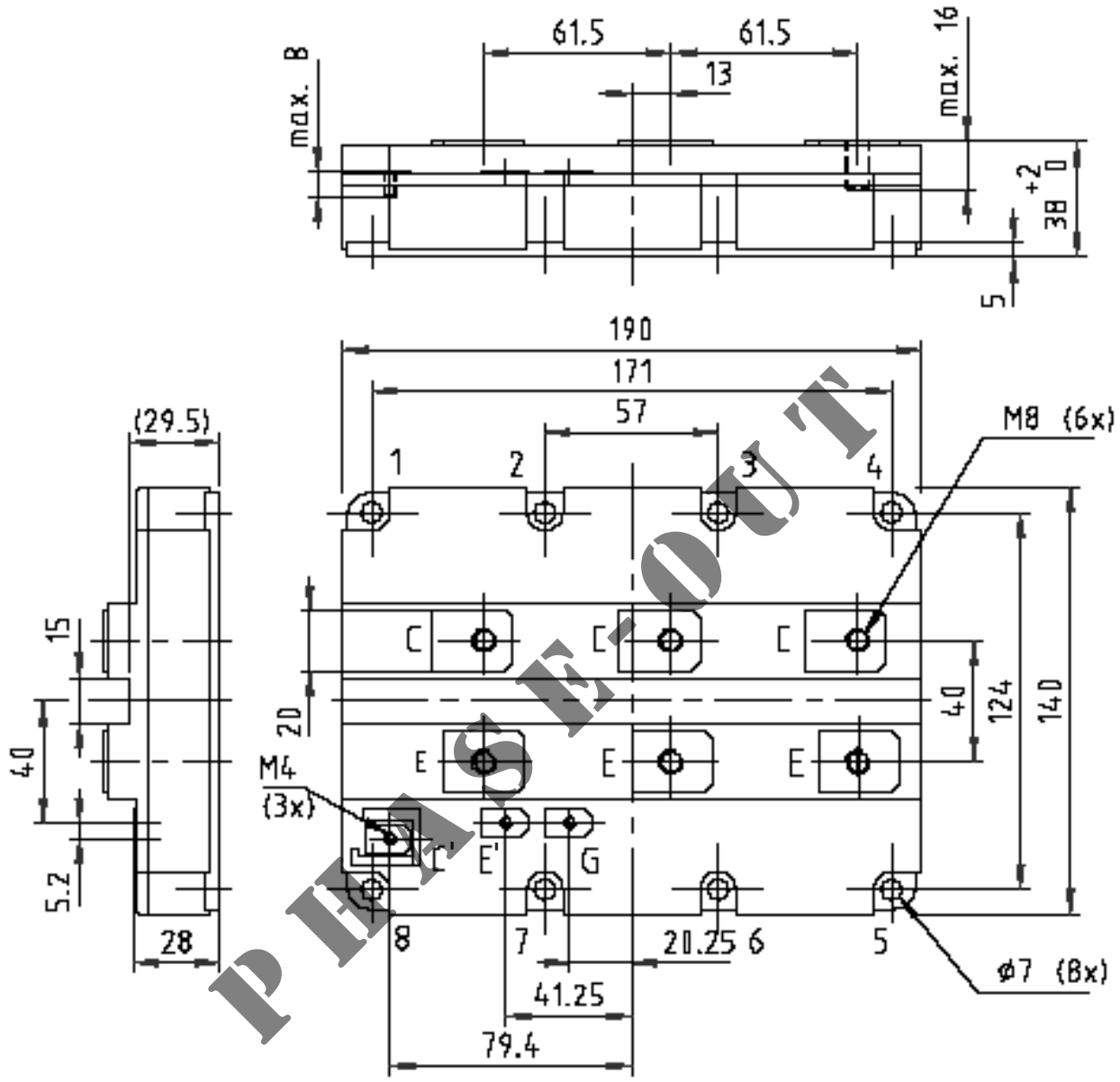
*) $V = V_{CE(sat)} + R_{term-chip} \cdot I_C$ resp. $V = V_F + R_{term-chip} \cdot I_F$

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Outline drawing



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Note: all dimensions are shown in mm

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